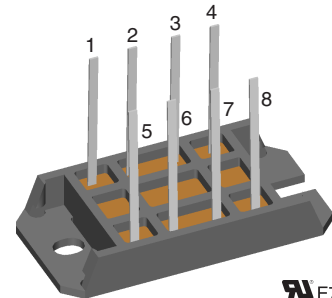
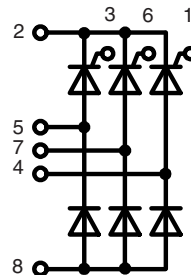


Three Phase Half Controlled Rectifier Bridge

$I_{dAVM} = 43 \text{ A}$
 $V_{RRM} = 1200-1600 \text{ V}$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1300	1200	VVZ 40-12io1
1500	1400	VVZ 40-14io1
1700	1600	VVZ 40-16io1



Symbol	Conditions	Maximum Ratings	
I_{dAV}	$T_K = 100^\circ\text{C}$; module	34	A
I_{dAVM}	module	43	A
I_{FRMS}, I_{TRMS}	per leg	25	A
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	320 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	340 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	510 A ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	485 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$	150 A/ μs
		non repetitive, $I_T = 1/3 \cdot I_{dAV}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000 V/ μs
V_{RGM}		10	V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	$\leq 10 \text{ W}$
		$t_p = 500 \mu\text{s}$	$\leq 5 \text{ W}$
		$t_p = 10 \text{ ms}$	$\leq 1 \text{ W}$
P_{GAVM}		0.5	W
T_{VJ}		-40...+125	$^\circ\text{C}$
T_{VJM}		125	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3600 V~
M_d	Mounting torque	(M5)	2-2.5 Nm
		(10-32 UNF)	18-22 lb.in.
Weight	typ.	28	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Soldering terminals
- UL registered E 72873

Applications

- Input rectifier for switch mode power supplies (SMPS)
- Softstart capacitor charging
- Electric drives and auxiliaries

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values	
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$	≤ 5 mA
		$T_{VJ} = 25^\circ\text{C}$	≤ 0.3 mA
V_F, V_T	$I_F, I_T = 30$ A, $T_{VJ} = 25^\circ\text{C}$	≤ 1.33 V	
V_{T0}	For power-loss calculations only	0.85 V	
r_T	($T_{VJ} = 125^\circ\text{C}$)	15 m Ω	
V_{GT}	$V_D = 6$ V;	$T_{VJ} = 25^\circ\text{C}$	≤ 1.0 V
		$T_{VJ} = -40^\circ\text{C}$	≤ 1.2 V
I_{GT}	$V_D = 6$ V;	$T_{VJ} = 25^\circ\text{C}$	≤ 65 mA
		$T_{VJ} = -40^\circ\text{C}$	≤ 80 mA
		$T_{VJ} = 125^\circ\text{C}$	≤ 50 mA
V_{GD}	$T_{VJ} = T_{VJM};$	$V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = T_{VJM};$	$V_D = 2/3 V_{DRM}$	≤ 5 mA
I_L	$I_G = 0.3$ A; $t_G = 30$ μs $di_G/dt = 0.3$ A/ μs	$T_{VJ} = 25^\circ\text{C}$	≤ 150 mA
		$T_{VJ} = -40^\circ\text{C}$	≤ 200 mA
		$T_{VJ} = 125^\circ\text{C}$	≤ 100 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 100 mA	
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 2 μs	
t_q	$T_{VJ} = 125^\circ\text{C}; I_T = 15$ A, $t_p = 300$ μs , $-di/dt = 10$ A/ μs	typ. 150 μs	
Q_r	$V_R = 100$ V, $dv/dt = 20$ V/ μs , $V_D = 2/3 V_{DRM}$	75 μC	
R_{thJC}	per thyristor (diode); DC current	1.0 K/W	
	per module	0.17 K/W	
R_{thJH}	per thyristor (diode); DC current	1.6 K/W	
	per module	0.27 K/W	
d_s	Creeping distance on surface	7 mm	
d_A	Creepage distance in air	7 mm	
a	Max. allowable acceleration	50 m/s ²	

Dimensions in mm (1 mm = 0.0394")

